



LTK4N/LTK6N SERIES

Breakdown voltage bigger better
(Ta = 25°C)

Model No.		Internal Connection Diagram	Outline Dimensions	Absolute Maximum Ratings		Electro-optical Characteristics								
				Collector-Emitter Voltage V_{CEO} (V)	Isolation Voltage V_{iso} (Vrms)	Current Transfer Ratio			Response Time				Collector Dark Current	
						CTR (%)MIN.	I_F (mA)	V_{CE} (V)	t_r (μ s)TYP.	I_C (mA)	R_L (Ω)	V_{CE} (V)	I_{CEO} (A)MAX.	V_{CE} (V)
Single Phototransistor Type	LTK4N25V	A	①	30	2,500	20	10	10	3 (t_r)	2	100	10	5×10^{-8}	10
	LTK4N26V				1,500		10	10						
	LTK4N28V				500		10	10						
	LTK4N35V				3,550	100	10	10	3 (t_{on})	2	100	$10(V_{CC})$	5×10^{-8}	10
	LTK4N37V				1,500	100	10	10						
Darlington Photo-transistor Type	LTK4N33	B		30	1,500	500	10	10	MAX. 5 (t_{on})	50	200mA (I_F) ($t_w \approx 1.0ms$)	$10(V_{CC})$	1×10^{-7}	10

(Ta = 25°C)

Model No.	Internal Connection Diagram	Outline Dimensions	Absolute Maximum Ratings		Electro-optical Characteristics											
			Output Current I_O (mA)	Isolation Voltage V_{iso} (Vrms)	Current Transfer Ratio				Propagation Time				Instantaneous Common Mode Rejection Voltage			
					CTR (%) MIN.	I_F (mA)	V_O (V)	V_{CC} (V)	t_{PLH} (μ s) TYP.	t_{PHL} (μ s) TYP.	I_F (mA)	R_L (Ω)	CM_H (V/ μ s) TYP.	I_F (mA)	V_{CM} (V_{P-P})	V_{CC} (V)
LTK6N136V	C	②	8	2,500	19	16	0.4	4.5	0.3	0.5	16	1,900	1,000	0	10	5
LTK6N139V	D		60		500	1.6	0.4	4.5	5	5	0.5	4,700	500	0	10	5

Internal Connection Diagrams

A	B	C	D
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Outline Dimensions

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